MT3S35T

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANER TYPE

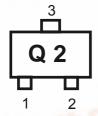
MT3S35T

VCO OSCILLETOR STAGE **UHF LOW NOISE AMPLIFIER APPLICATION**

FEATURES

- Low Noise Figure :NF=1.4dB (@f=2GHz)
- High Gain:|S21e|²=13.0dB (@f=2GHz) WWW.DZSC.COM

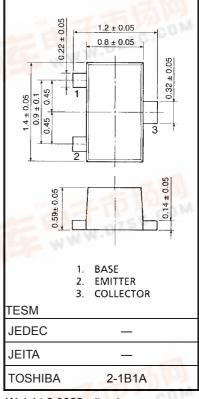
Marking



Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-Base voltage	V _{CBO}	8	V	
Collector-Emitter voltage	V _{CEO}	4.5	V	
Emitter-Base voltage	V _{EBO}	1.5	V	
Collector-Current	Ic	24	mA	
Base-Current	I _B	12	mA	
Collector Power dissipation	PC	100	mW	
Junction temperature	Tj	150	°C	
Storage temperature Range	T _{stg}	-55~150	°C	

Unit: mm



Weight:0.0022g (typ.) = WWW.



Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition Frequency	fT	V _{CE} =3V, I _C =10mA, f=2GHz	16	20	-	GHz
Insertion Gain	S21e ² (1)	V _{CE} =3V, I _C =10mA, f=1GHz	16	18	-	dB
	S21e ² (2)	V _{CE} =3V, I _C =10mA, f=2GHz	11	13	-	dB
Noise Figure	NF(1)	V _{CE} =3V, I _C =2mA, f=1GHz	-	1.1	-	dB
	NF(2)	V _{CE} =3V, I _C =2mA, f=2GHz	-	1.4	1.9	dB

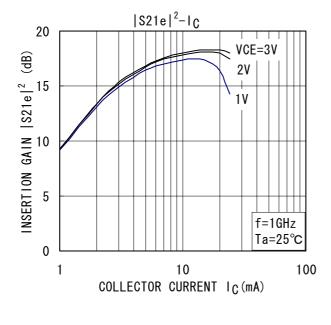
Electrical Characteristics (Ta = 25°C)

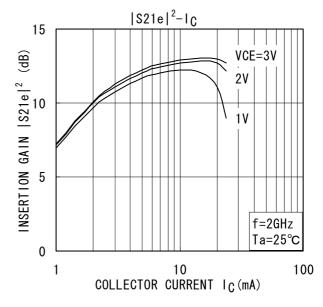
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector Cut-off Current	I _{CBO}	V _{CB} =8V, I _E =0	-	-	1	μΑ
Emitter Cut-off Current	I _{EBO}	V _{EB} =1V, I _C =0	-	-	1	μA
DC Current Gain	hFE	V _{CE} =3V, I _C =10mA	70	-	140	-
Output Capacitance	C _{ob}	V _{CB} =1V, I _E =0, f=1MHz	-	0.46	0.75	pF
Reverse Transistor Capacitance	C _{re}	V _{CB} =1V, I _E =0, f=1MHz (Note 1)	-	0.21	0.4	pF

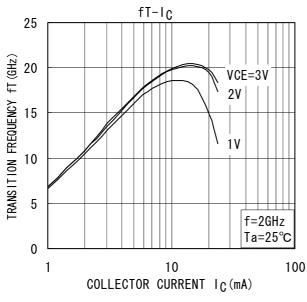
Note 1: Cre is measured by 3 terminal method with capacitance bridge.

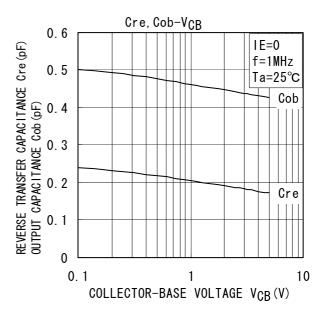
Caution: This device is sensitive to electrostatic discharge.

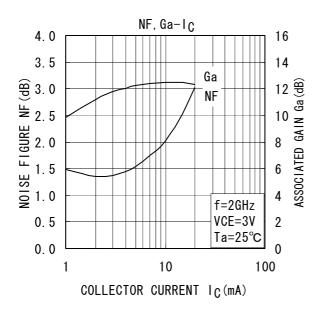
Please make enough tool and equipment earthed when you handle.



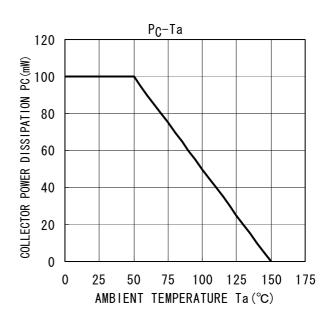








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